

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = -250 V
- Complementary to 2STC5948
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Application

■ Audio power amplifier

Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

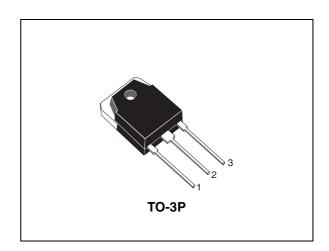


Figure 1. Internal schematic diagram

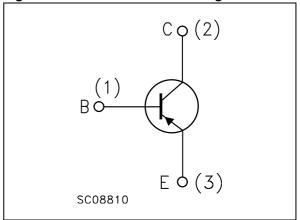


Table 1. Device summary

Order code	Marking	Package	Packaging	
2STA2120	2STA2120	TO-3P	Tube	

Electrical ratings 2STA2120

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter		Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-250	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-250	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	-6	V
Ic	Collector current	-17	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-34	Α
P _{TOT}	Total dissipation at T _C = 25 °C	200	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

•	Symbol	Parameter		Value	Unit
ı	R _{thj-case}	Thermal resistance junction-case	max	0.625	°C/W

2 Electrical characteristics

($T_{case} = 25 \, ^{\circ}C$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test condit	ions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = -250 V				-5	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -6 V				-5	μΑ
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -50 mA		-250			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA		-250			V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = -1 mA		-6			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C = -8 A I _B =	= -800 mA			-3	V
V _{BE} (1)	Base-emitter voltage	$I_C = -7 \text{ A} \qquad V_C$	_E = -5 V			-1.5	V
h _{FE}	DC current gain	I _C = -1 A V _C I _C = -7 A V _C	_	80 35		160	
f _T	Transition frequency	$I_C = -1 A V_C$	_E = -5 V		25		MHz

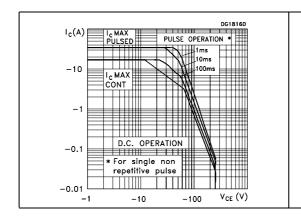
^{1.} Pulsed duration = 300 µs, duty cycle ≤1.5%

Electrical characteristics 2STA2120

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



Ptot (%)

100

80

60

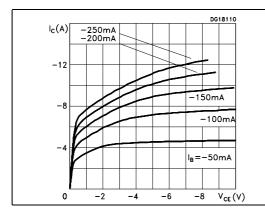
40

20

0 25 50 75 100 125 T_{case}(°C)

Figure 4. Output characteristics

Figure 5. DC current gain



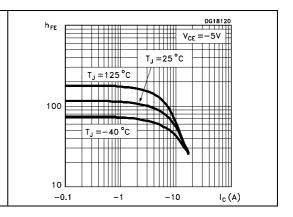
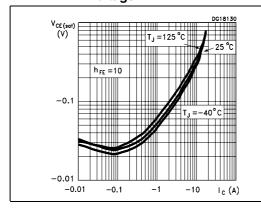
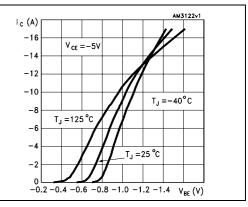


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter voltage





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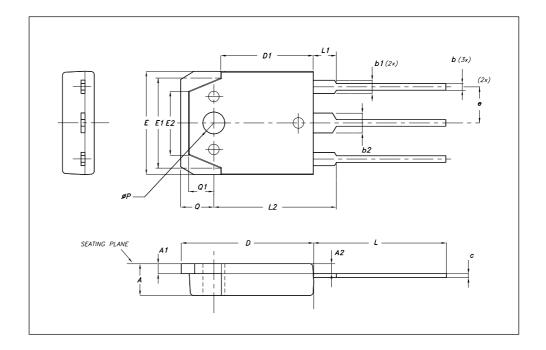
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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TO 2D	Machan	ical data
1U-3P	wecnan	icai data

DIM.		mm.	
	MIN.	TYP	MAX.
Α	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
Р	3.10		3.30
Q		5	
Q1		3.80	



2STA2120 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes	
23-Nov-2007	1	Initial release	
09-May-2008	2	Added new graphics.	
07-Nov-2008	3	Document status promoted from preliminary data to datasheet.	

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